TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS V)

TPCA8106

 $(V_{GS} = -10V)$

Lithium Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance: R_{DS} (ON) = 2.9 m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 79S$ (typ.)
- Low leakage current: $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode: $V_{th} = -0.8$ to -2.0 V ($V_{DS} = -10$ V, $I_D = -1$ mA)

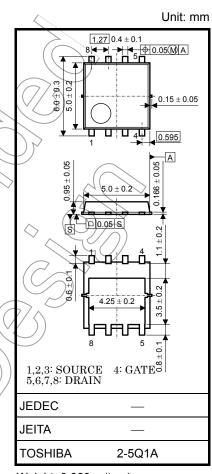
Absolute Maximum Ratings (Ta = 25°C)

			$(\cap$	
Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	-30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	-30	V
Gate-source voltage		V _{GSS} \langle	±20	Y
Drain current	DC (Note 1)	ID (-40	$\langle \rangle$
	Pulsed (Note 1)	IDP	-120	A
Drain power dissipation (Tc=25°C)		PB	45	w
Drain power dissipation $(t = 10 s)$ (Note 2a).		PD	2.8	W
Drain power dissipation	· · · · · · · · · · · · · · · · · · ·	P D	1.6	w
Single pulse avalanche energy (Note 3)		EAS	208	mJ
Avalanche current		IAR	-40	А
Repetitive avalanche energy $(Tc = 25^{\circ}C)$ (Note 4)		EAR	4.5	mJ
Channel temperature		Tch	150	°C
Storage temperature range		Tstg	-55 to 150	°C

Note: For Note 1 to 4, please refer to the next page.

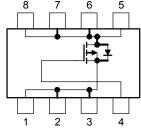
Using continuously under heavy loads (e.g. the application of high 1 2 3 4 temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

Circuit Configuration

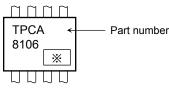


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Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case (Tc=25°C)	R _{th (ch-c)}	2.78	°C/W	
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W	

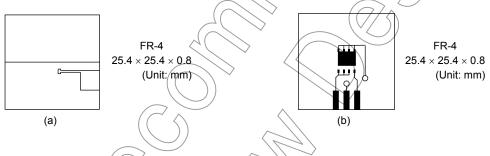
Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2:

(a) Device mounted on a glass-epoxy board (a)



- Note 3: $V_{DD} = -24 \text{ V}, T_{ch} = 25 \text{ C}$ (initial), L = 100 µH, RG = 25 Ω , VAR = -40 A
- Note 4: Repetitive rating: pulse width limited by max channel/temperature
- Note 5: * Weekly code: (Three digits)

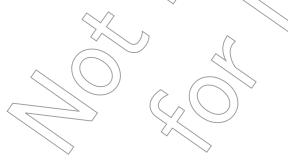


Electrical Characteristics (Ta = 25°C)

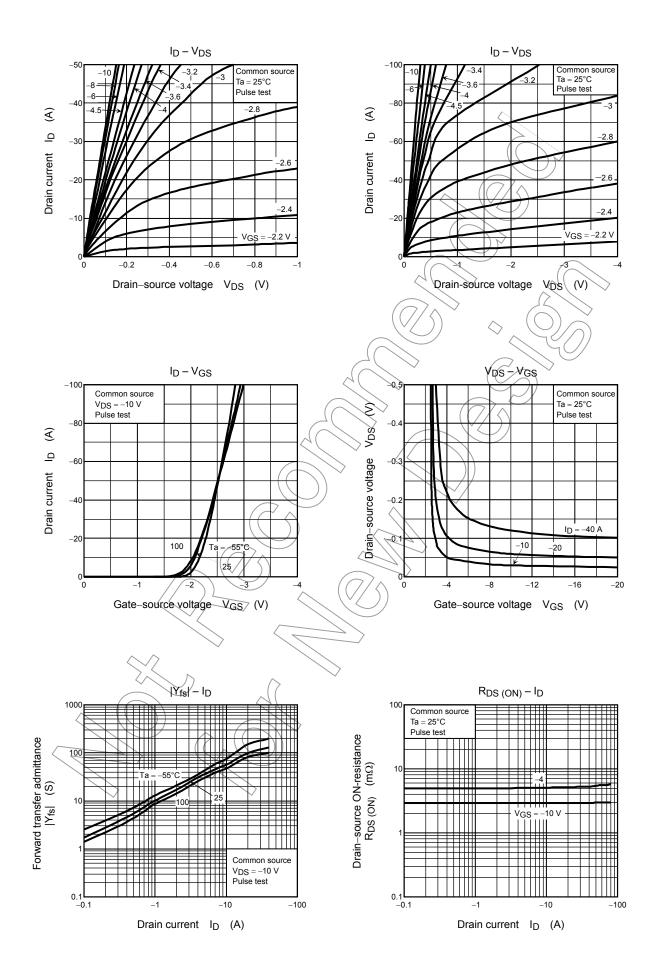
Ch	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	rrent	I _{GSS}	$V_{GS}=\pm 20~V,~V_{DS}=0~V$	_	_	±100	nA	
Drain cut-OFF cu	urrent	I _{DSS}	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_		-10	μA	
Drain-source breakdown voltage		V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	_	_	v	
		V (BR) DSX	$I_D = -10$ mA, $V_{GS} = 20$ V	-13		_		
Gate threshold v	oltage	V _{th}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	-0.8	-7(-2.0	V	
Drain-source ON-resistance		R _{DS (ON)}	$V_{GS} = -4 V, I_D = -20 A$		5.5	7.8	- mΩ	
			$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -20 \text{ A}$	\mathcal{A}	2.9	3.7		
Forward transfer	admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -20 \text{ A}$	39.5	79	—	S	
Input capacitance		C _{iss}		_	4600	_		
Reverse transfer capacitance		C _{rss}	$V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz$		970		pF	
Output capacitance		C _{oss}		_	1500	\searrow		
Switching time	Rise time	tr		-(C	10	>		
	Turn-ON time	t _{on}	$V_{GS} = 0$ V_{OUT}		20	_	20	
	Fall time	t _f		$\widehat{\mathcal{A}}$	300		ns	
	Turn-OFF time	toff	$V_{DD} = 15$ Duty $\leq 1\%$, t _w = 10 μ s) —	750	_		
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ -24 V, V _{GS} = -10 V,	_	130			
Gate-source charge 1		Q _{gs1}	I _D = -40 A	_	12	—	nC	
Gate-drain ("miller") charge		Qgd	\sim	_	40	_		

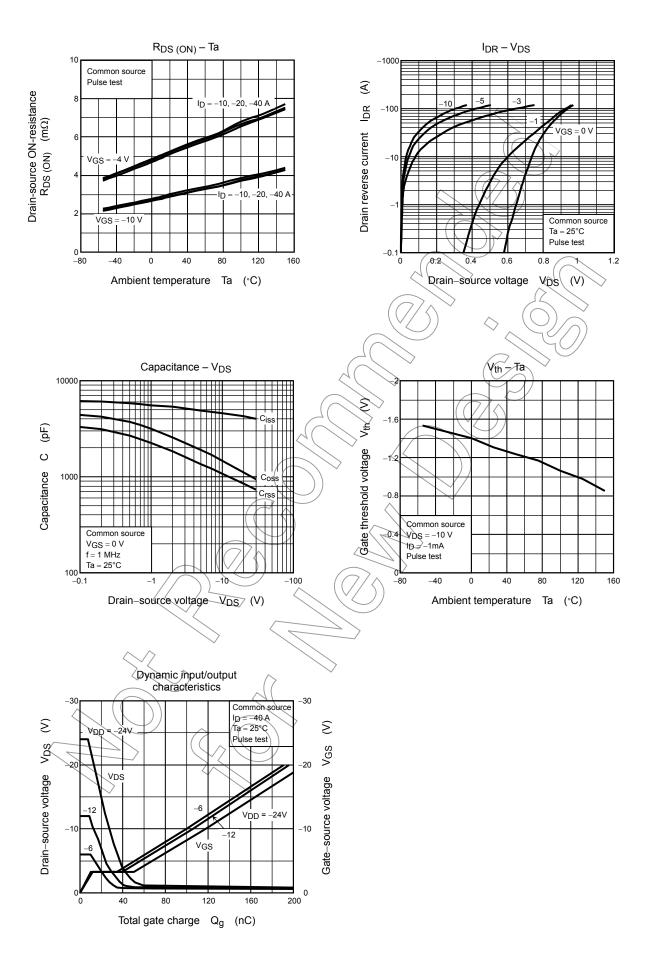
Source-Drain Ratings and Characteristics ($Ta = 25^{\circ}C$)

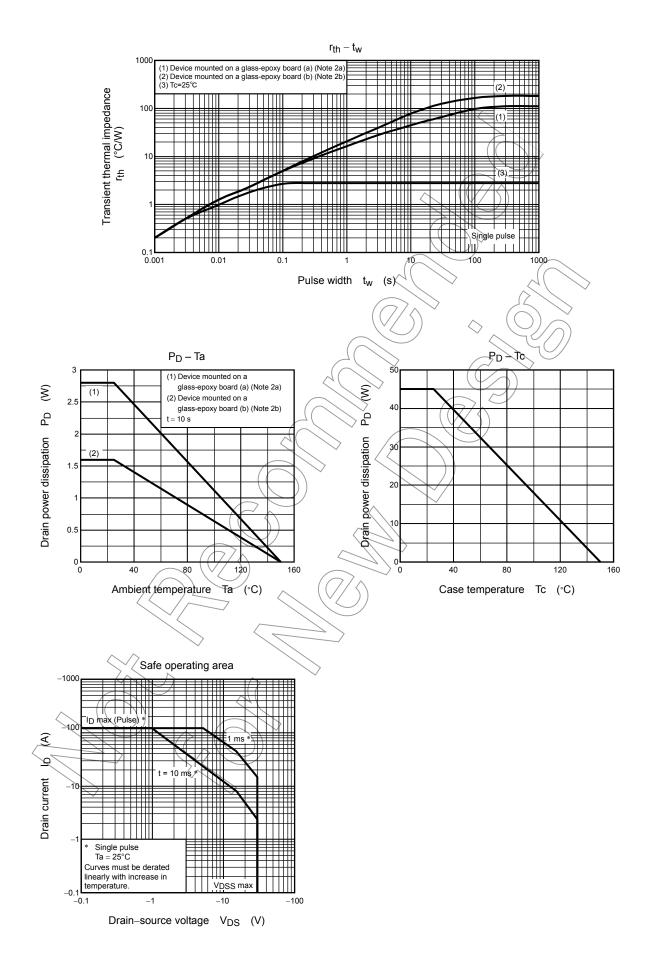
Characteristics	Symbol	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I _{DRP} —			-120	А
Forward voltage (diode)	V_{DSE} IDR = 40 A, V_{GS} = 0 V			1.2	V



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